

Silicon PNP Power Transistors

2SB1052

DESCRIPTION

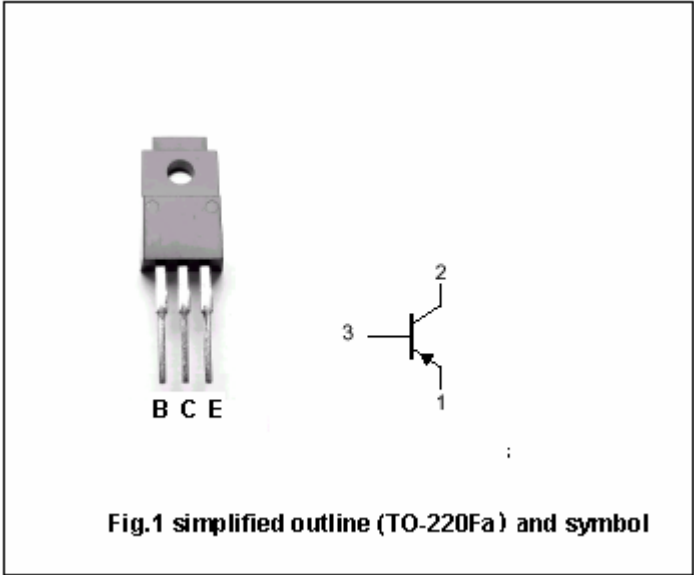
- With TO-220Fa package
- Complement to type 2SD1480
- Low collector saturation voltage

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-60	V
V _{CEO}	Collector -emitter voltage	Open base	-60	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-2	A
I _{CM}	Collector current-peak		-4	A
P _C	Collector power dissipation	T _a =25	2.0	W
		T _C =25	25	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-30mA; I _B =0	-60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A ; I _B =-0.2A			-2.0	V
V _{BE}	Base-emitter on voltage	I _C =-1A ; V _{CE} =-4V			-1.2	V
I _{CES}	Collector cut-off current	V _{CE} =-60V; V _{BE} =0			-0.2	mA
I _{CEO}	Collector cut-off current	V _{CE} =-30V; I _B =0			-0.3	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-1.0	mA
h _{FE-1}	DC current gain	I _C =-0.1A ; V _{CE} =-4V	35			
h _{FE-2}	DC current gain	I _C =-1A ; V _{CE} =-4V	40		250	

Switching times

t _{on}	Turn-on time	I _C =-1A ; I _{B1} =-I _{B2} =-0.1A		0.1		μs
t _{stg}	Storage time			1.5		μs
t _f	Fall time			0.3		μs

◆ h_{FE-2} Classifications

R	Q	P
40-90	70-150	120-250

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PACKAGE OUTLINE

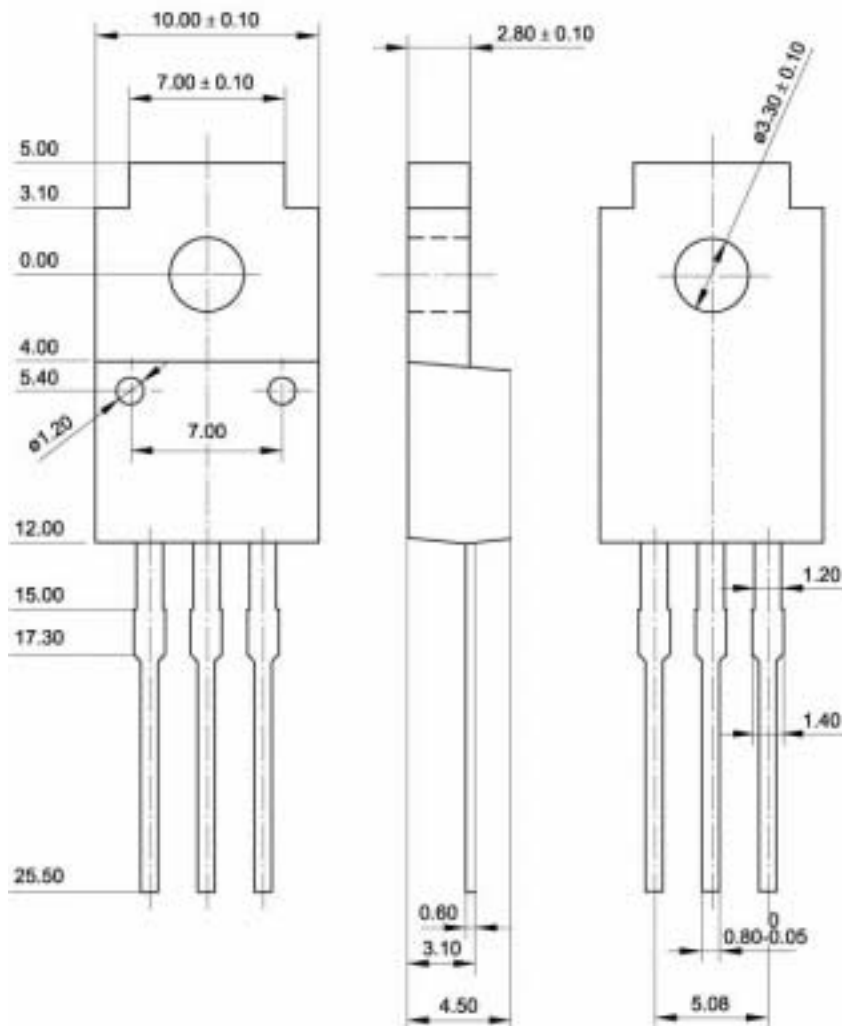


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)